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(54) **METHOD FOR FORMING FIN-SHAPED STRUCTURE**

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CPC **H01L 29/7853** (2013.01); **H01L 29/66795** (2013.01)

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None
See application file for complete search history.

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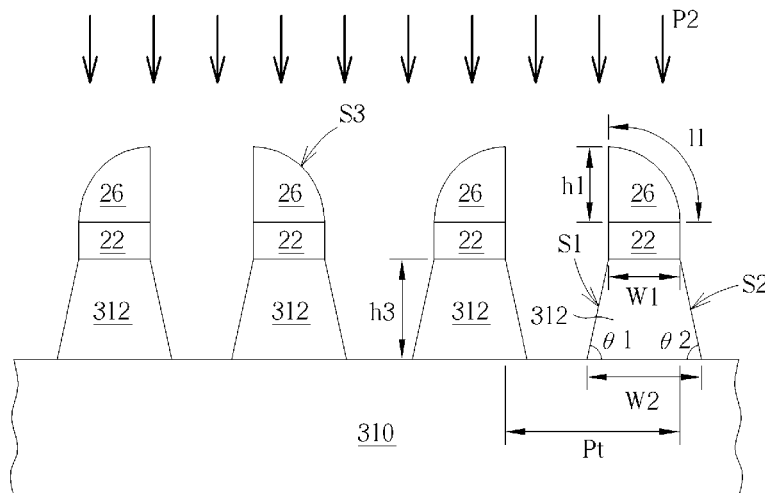
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(57) **ABSTRACT**

A method for forming a fin-shaped structure includes the following steps. A pad layer is formed on a substrate. A sacrificial pattern is formed on the pad layer. A spacer is formed on the pad layer beside the sacrificial pattern, wherein the ratio of the height of the spacer to the pad layer is larger than 5. The sacrificial pattern is removed. The layout of the spacer is transferred to the substrate to form at least a fin-shaped structure having a taper profile in the substrate.

17 Claims, 5 Drawing Sheets



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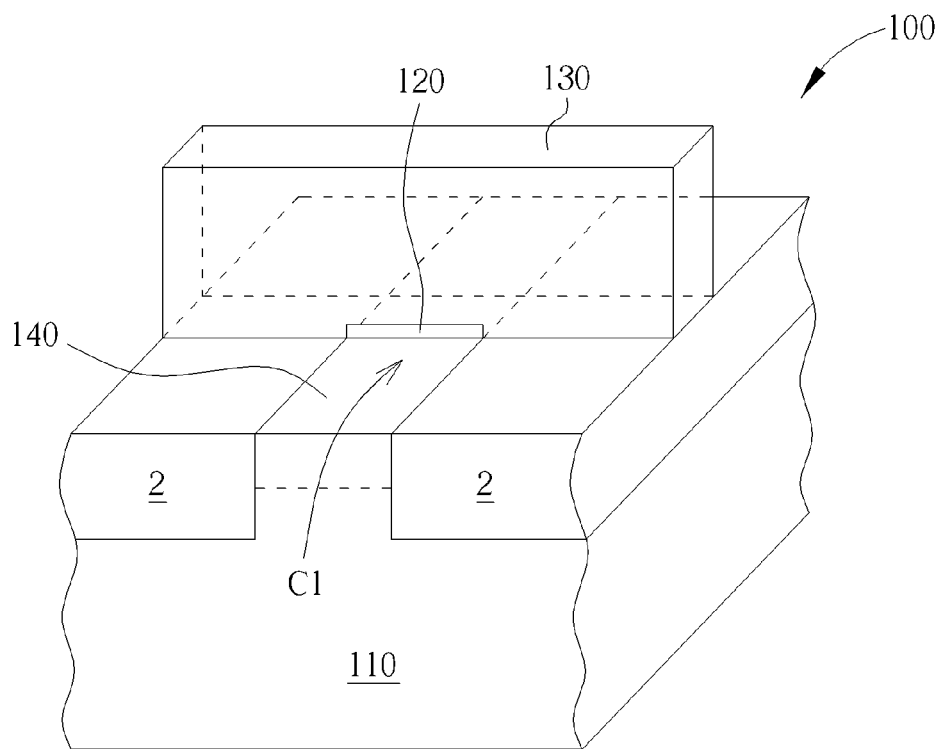


FIG. 1

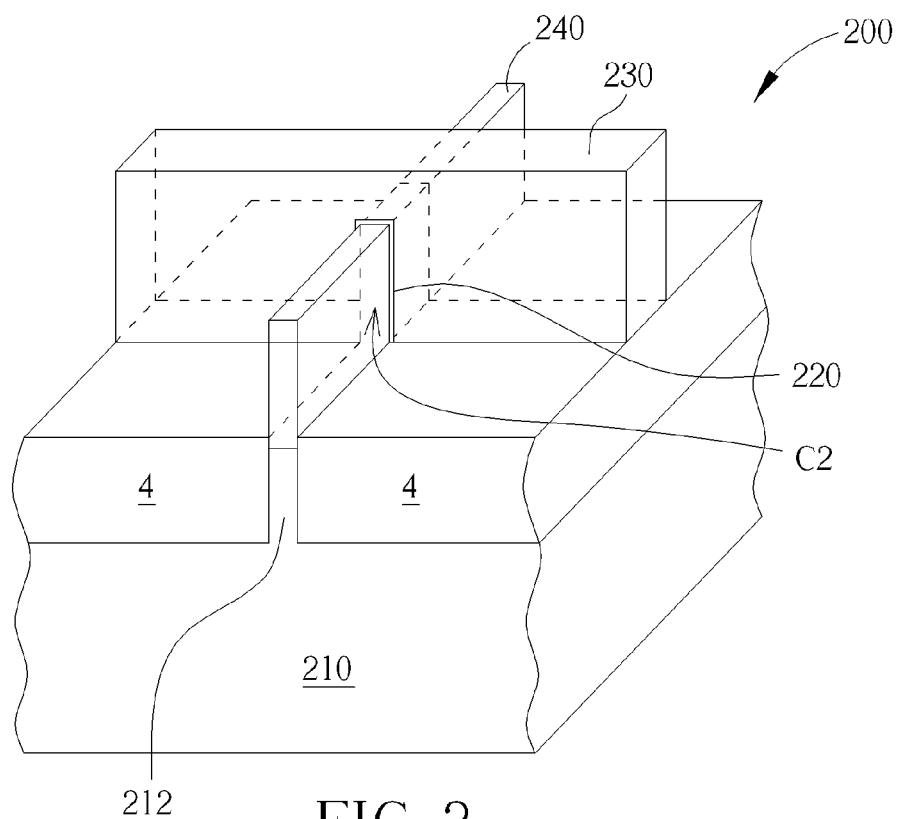


FIG. 2

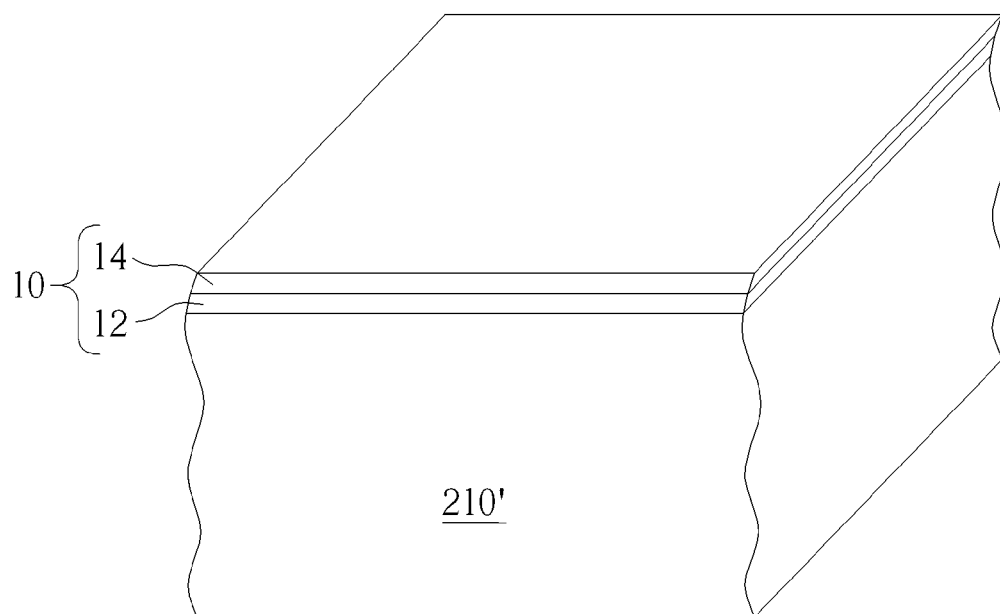


FIG. 3

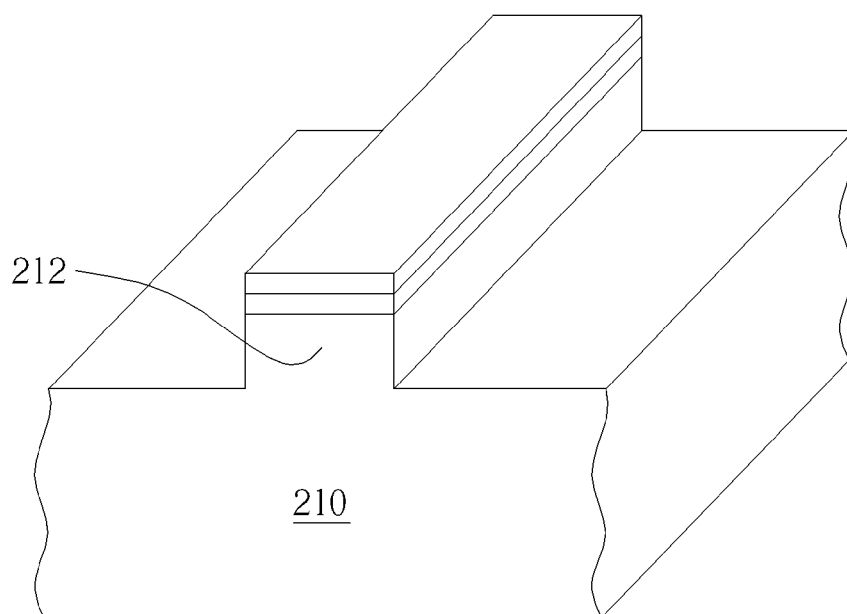


FIG. 4

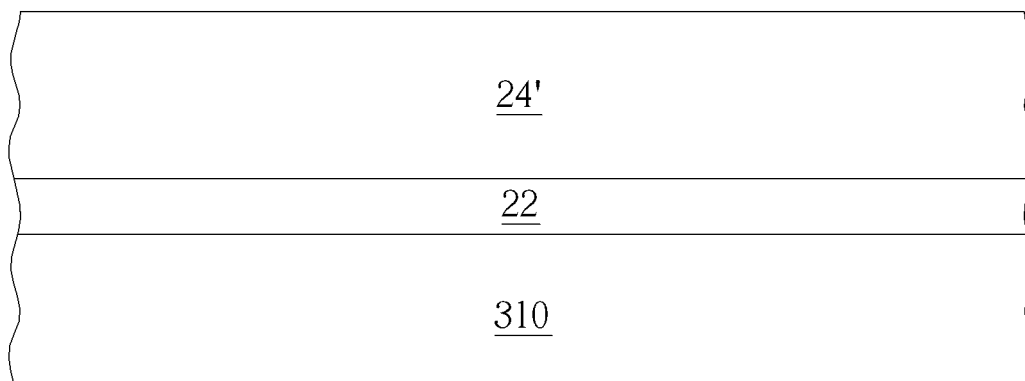


FIG. 5



FIG. 6

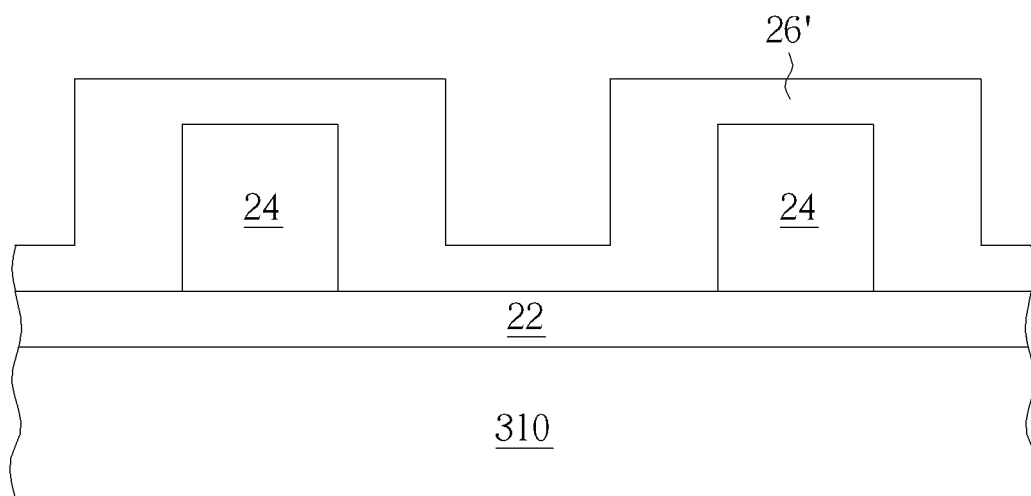


FIG. 7

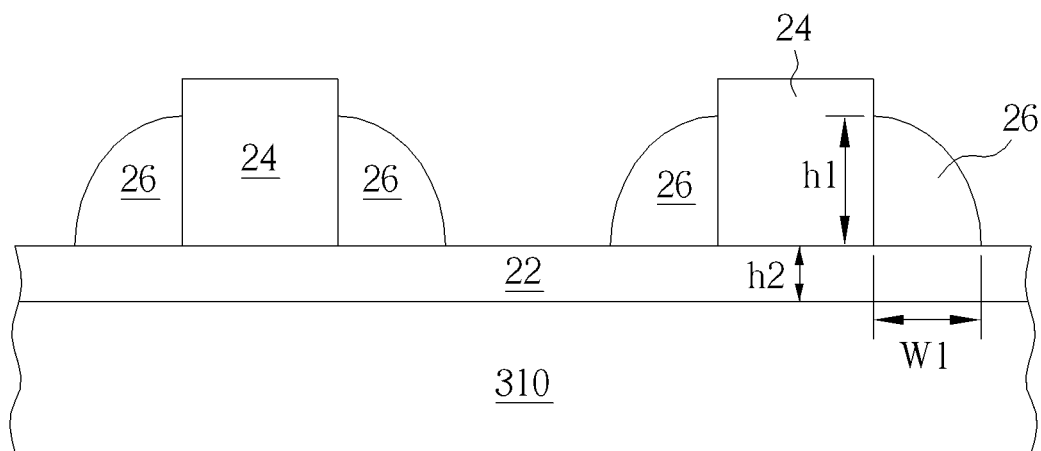


FIG. 8

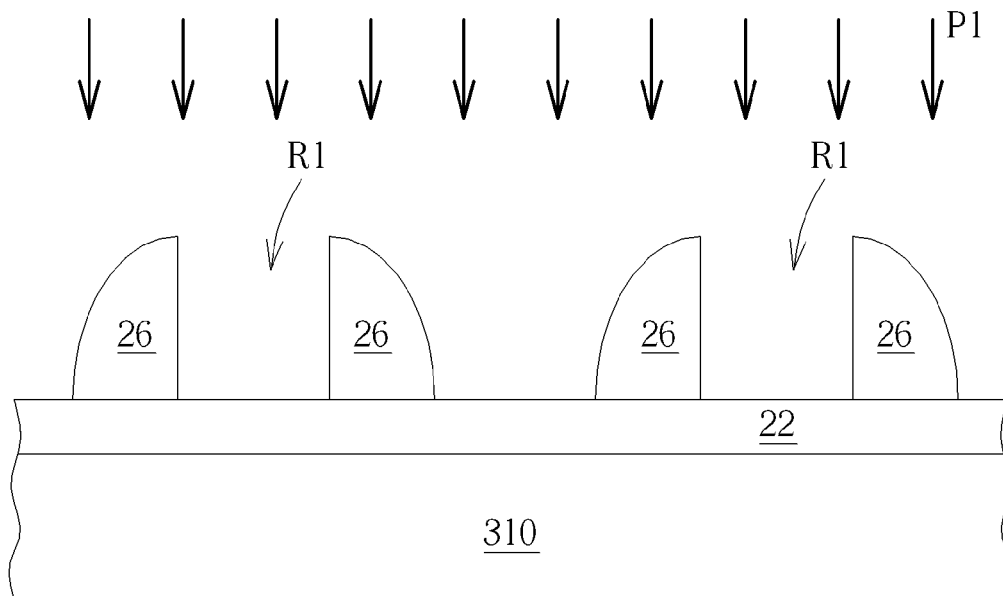


FIG. 9

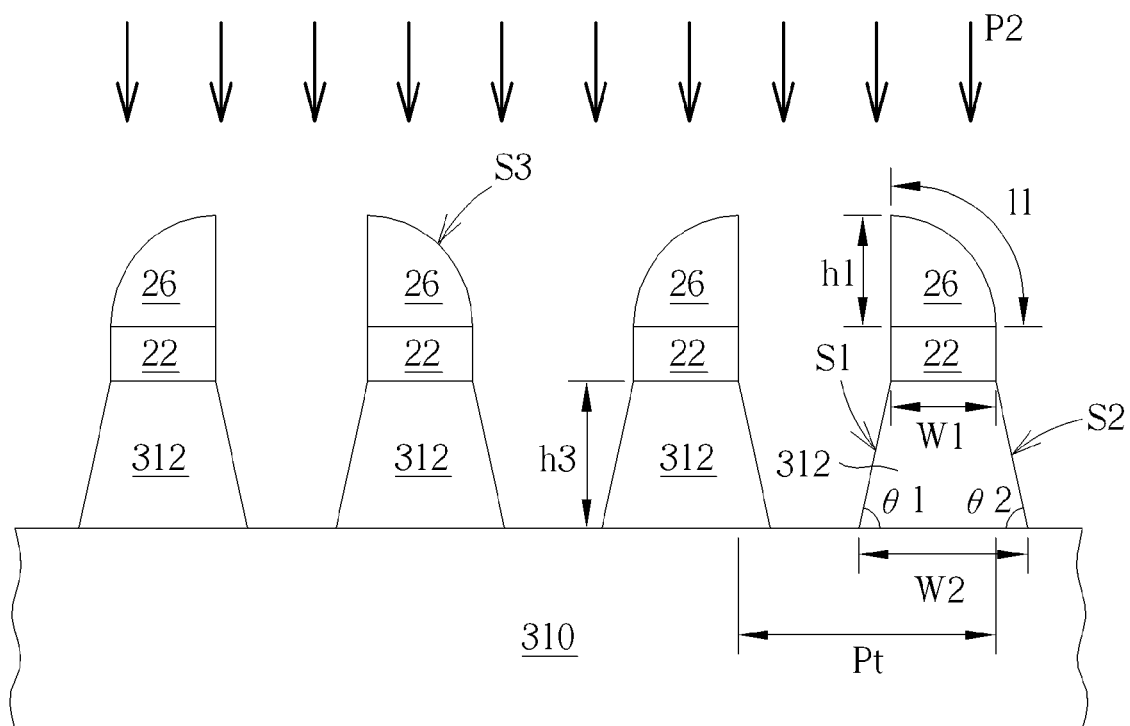


FIG. 10

METHOD FOR FORMING FIN-SHAPED STRUCTURE

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates generally to a method for forming a fin-shaped structure, and more specifically to a method for forming a fin-shaped structure having a taper profile.

2. Description of the Prior Art

With the increasing miniaturization of semiconductor devices, various multi-gate MOSFET devices have been developed. The multi-gate MOSFETs are advantageous for the following reasons. First, the manufacturing processes of the multi-gate MOSFET devices can be integrated into traditional logic device processes, and thus are more compatible. In addition, since the three-dimensional structure of a multi-gate MOSFET increases the overlapping area between the gate and the substrate, its channel region is controlled more effectively. This therefore reduces drain-induced barrier lowering (DIBL) effect and short channel effect. Moreover, the channel region is longer for a similar gate length. Therefore, the current between the source and the drain is increased.

However, as the size of the multi-gate MOSFETs shrink, the electrical and physical requirements in each parts of the multi-gate MOSFET become critical, like the sizes and shapes of the fin-shaped structures and the spacings between each fin-shaped structures for example. Thus, how to reach standard requirements and overcome these physical limitations has become an important issue in the industry of the multi-gate MOSFETs.

SUMMARY OF THE INVENTION

The present invention provides a method for forming a fin-shaped structure wherein the fin-shaped structure has a taper profile in order to improve the processing qualities and to simplify the process.

The present invention provides a method for forming a fin-shaped structure including the following steps. A pad layer is formed on a substrate. A sacrificial pattern is formed on the pad layer. A spacer is formed on the pad layer beside the sacrificial pattern, wherein the ratio of the height of the spacer to that of the pad layer is larger than 5. The sacrificial pattern is then removed. The layout of the spacer is further transferred into the substrate to form at least a fin-shaped structure having a taper profile in the substrate.

According to the above, the present invention provides a method for forming a fin-shaped structure, which forms at least a fin-shaped structure having a taper profile in a substrate by transferring the layout of spacers into the substrate. It is emphasized that, the height ratio of the spacer to the pad layer in the present invention is larger than 5, so the fin-shaped structure of the present invention can be formed. For example, the fin-shaped structure formed through this method has a taper profile. Preferably, the maximum width of the fin-shaped structure is in a range of 5~20 nanometers, and the pitch between each of the fin-shaped structures can approach 70 nanometers.

These and other objectives of the present invention will no doubt become obvious to those of ordinary skill in the art after reading the following detailed description of the preferred embodiment that is illustrated in the various figures and drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 schematically depicts a three-dimensional diagram of a planar transistor according to a first embodiment of the present invention.

FIG. 2 schematically depicts a three-dimensional diagram of a multi-gate MOSFET according to a second embodiment of the present invention.

FIGS. 3-4 schematically depict cross-sectional views of a method for forming a fin-shaped structure according to the second embodiment of the present invention.

FIGS. 5-10 schematically depict cross-sectional views of a method for forming a fin-shaped structure according to a third embodiment of the present invention.

DETAILED DESCRIPTION

A semiconductor chip may include a plurality of electrical circuit areas, such as core electrical circuit areas, logical electrical circuit areas, input/output electrical circuit areas, static random access memory (SRAM) electrical circuit areas etc. Planar transistors or/and non-planar transistors with different electrical types may be needed to be formed in each area, and the selection and integration of planar transistors or/and non-planar transistors depend upon the needed functions. Structures of planar transistors and non-planar transistors are illustrated in the following.

FIG. 1 schematically depicts a three-dimensional diagram of a planar transistor according to a first embodiment of the present invention. As shown in FIG. 1, a planar transistor 100 includes a substrate 110, at least an isolation structure 2, a gate dielectric layer 120, an electrode 130 and a source/drain region 140. The substrate 110 may be a semiconductor substrate such as a silicon substrate, a silicon containing substrate such as a silicon carbide substrate, a III-V group-on-silicon (such as GaN-on-silicon) substrate, a graphene-on-silicon substrate, a silicon-on-insulator (SOI) substrate or an epitaxial layer containing a substrate such as a P-type substrate with a 2.5 μm P-type epitaxial layer. The isolation structure 2 is located in the substrate 110, wherein the isolation structure 2 is used to isolate each transistor formed on the substrate 110. The isolation structure 2 may be a shallow trench isolation (STI) structure, which may be formed through a shallow trench isolation (STI) process; or, the isolation structure 2 may be a deep trench isolation (DTI) structure, which may be formed through a deep trench isolation (DTI) process, wherein the depth of the shallow trench isolation (STI) structure may be comprised within a range of 2500~4000 angstroms, and the depth of the deep trench isolation (DTI) structure may be comprised within a range of 25000~36000 angstroms, but it is not limited thereto, and the forming methods are known in the art so as not to describe herein.

The gate dielectric layer 120 is located between the substrate 110 and the electrode 130. The gate dielectric layer 120 may be an oxide layer (SiO_2), which may be formed through a thermal oxide process or a chemical oxide process, and has a “-”-shaped cross-sectional profile. The electrode 130 may be a word line crossing a plurality of transistors, and the material may be polysilicon, thereby constituting a polysilicon gate. The source/drain region 140 is located in the substrate 110 beside the electrode 130 and the gate dielectric layer 120, wherein the dopant of the source/drain region 140 depends upon the electrical type of the formed planar transistor 100. For instance, if the planar transistor 100 is an N-type transistor, the dopant of the source/drain region 140 may be pentavalent ions such as phosphorus; if the planar transistor 100 is a P-type transistor, the dopant of the source/drain

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region **140** may be trivalent ions, such as boron. Then, later semiconductor processes may be performed to electrically connect the electrode **130** and the source/drain region **140** outwards. Moreover, strained-silicon technology processes may be performed to induce strain on a semiconductor crystal thereby altering the speed at which charges move through that crystal. Strain makes MOS transistors work better by enabling electrical charges, such as electrons, to pass more easily through the silicon lattice of the gate channel.

Furthermore, the planar transistor **100** may include a spacer (not shown) located on the substrate **110** beside the electrode **130** and the gate dielectric layer **120**. Therefore, a metal gate replacement process may be performed in later processes. When a gate last for high-k last process is applied, the metal gate replacement process is performed to remove the electrode **130** and the gate dielectric layer **120** surrounded by the spacer (not shown) sequentially, and then the gate dielectric layer **120** is replaced by other denser buffer layers and dielectric layers having a high dielectric constant while the electrode **130** is replaced by a metal electrode, so that a metal gate including a work function metal layer and a low resistivity material is formed, but it is not limited thereto. In another embodiment, the gate dielectric layer **120** may not be removed and may be used as a buffer layer, and a dielectric layer having a high dielectric constant is directly formed thereon. In addition, when a gate last for high-k first process is applied, the gate dielectric layer **120** already includes a gate dielectric layer having a high dielectric constant, so that a metal gate replacement process is performed to remove the electrode **130** only, and replaces it by a metal electrode, so that a metal gate including a work function metal layer and a low resistivity material is formed, but it is not limited thereto. Moreover, the gate dielectric layer **120** may further include a buffer layer (not shown) located between the substrate **110** and a dielectric layer having a high dielectric constant. In other ways, the planar transistor **100** may be a transistor having a polysilicon gate or may be formed through applying a gate first process or etc.

Whether the planar transistor **100** has a polysilicon gate or a metal gate, the gate channel C1 is located below the gate dielectric layer **120** and in the substrate **110** between the source/drain region **140**, and therefore has a “—”-shaped cross-sectional profile.

However, with the increasing miniaturization of the semiconductor devices, various Fin-shaped field effect transistor (FinFET) devices have been developed. The Fin-shaped field effect transistor (FinFET) is advantageous for the following reasons. First, manufacturing processes of Fin-shaped field effect transistor (FinFET) devices can be integrated into traditional logic device processes, and thus are more compatible. In addition, since the three-dimensional structure of the FinFET increases the overlapping area between the gate and the substrate, the channel region is controlled more effectively. This therefore reduces drain-induced barrier lowering (DIBL) effects and short channel effects. Moreover, the channel region is longer for a similar gate length. Therefore, the current between the source and the drain is increased. Thus, multi-gate MOSFETs and processes thereof are presented in the following. Besides, different numbers of fin-shaped structures may be described in different steps of these embodiments to simplify and clarify the present invention, and common components are represented by common symbols, but the numbers of applied fin-shaped structures in each step are not restricted.

FIG. 2 schematically depicts a three-dimensional diagram of a multi-gate MOSFET according to a second embodiment of the present invention. In FIG. 2 one example of a multi-gate

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MOSFET—a tri-gate MOSFET—is shown. A tri-gate MOSFET **200** may include a substrate **210**, a fin-shaped structure **212**, at least an isolation structure **4**, a gate dielectric layer **220**, an electrode **230** and a source/drain region **240**.

The fin-shaped structure **212** is located on the substrate **210**. Generally, the fin-shaped structure **212** and the substrate **210** form one piece only, but the fin-shaped structure **212** may be additionally formed on the substrate **210**, depending upon the needs. The substrate **210** may be a semiconductor substrate such as a silicon substrate, a silicon containing substrate such as a silicon carbide substrate, a III-V group-on-silicon (such as GaN-on-silicon) substrate, a graphene-on-silicon substrate, a silicon-on-insulator (SOI) substrate or an epitaxial layer containing substrate such as a P-type substrate with a 2.5 μm P-type epitaxial layer. Moreover, the substrate **210** may have desired crystalline surfaces for later semiconductor processes; for example, the etching direction of an etching process may depend on the crystalline surfaces to etch desired shapes of recesses or trenches. The isolation structure **4** is located on the substrate **210** beside the fin-shaped structure **212**, wherein the isolation structure **4** is used to isolate each transistor formed on the substrate **210**. The isolation structure **4** may be a shallow trench isolation (STI) structure, which may be formed through a shallow trench isolation (STI) process, or the isolation structure **4** may be a deep trench isolation (DTI) structure, which may be formed through a deep trench isolation (DTI) process, wherein the depth of the shallow trench isolation (STI) structure may be comprised within a range of 2500~4000 angstroms, and the depth of the deep trench isolation (DTI) structure may be comprised within a range of 25000~36000 angstroms, but not limited thereto, and the forming methods are known in the art so as not to describe herein.

The gate dielectric layer **220** covers a part of the fin-shaped structure **212**, and is located between the fin-shaped structure **212** and the electrode **230**. The gate dielectric layer **220** has a “ \cap ”-shaped cross-sectional profile. The gate dielectric layer **220** may be a silicon oxide, which may be formed through a thermal oxide process or a chemical oxide process, but it is not limited thereto. The electrode **230** is disposed across a plurality of transistors and may be a word line or etc. The material of the electrode **230** may be polysilicon, thereby forming a polysilicon gate.

The source/drain region **240** is located in the fin-shaped structure **212** beside the electrode **230** and the gate dielectric layer **220**, wherein the dopants of the source/drain region **240** depend upon the electrical type of the formed tri-gate MOSFET **200**. For instance, if the tri-gate MOSFET **200** is an N-type transistor, the dopants of the source/drain region **240** may be pentavalent ions such as phosphorus; and if the tri-gate MOSFET **200** is a P-type transistor, the dopants of the source/drain region **240** may be trivalent ions such as boron. Later semiconductor processes may be carried out to electrically connect the electrode **230** and the source/drain region **240**. Moreover, strained-silicon technologies may be applied to induce strain on a semiconductor crystal, thereby altering the speed at which charges move through that crystal. Strain makes MOS transistors work better by enabling electrical charges, such as electrons, to pass more easily through the silicon lattice of the gate channel.

Furthermore, the tri-gate MOSFET **200** may include a spacer (not shown) located on the substrate **210** and the fin-shaped structure **212** beside the electrode **230** and the gate dielectric layer **220**. Therefore, a metal gate replacement process may be performed in later processes. When a gate last for high-k last process is applied, the metal gate replacement process is performed to remove the electrode **230** and the gate

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dielectric layer **220** surrounded by the spacer (not shown) sequentially, and then the gate dielectric layer **220** is replaced by another denser buffer layer and dielectric layer having a high dielectric constant while the electrode **230** is replaced by a metal electrode, so that a metal gate including a work function metal layer and a low resistivity material is formed, but it is not limited thereto. In another embodiment, the gate dielectric layer **220** may not be removed and may be used as a buffer layer, and a dielectric layer having a high dielectric constant is directly formed thereon. In addition, when a gate last for high-k first process is applied, the gate dielectric layer **220** already includes a gate dielectric layer having a high dielectric constant, so a metal gate replacement process is performed to remove the electrode **230** only which is then replaced by a metal electrode, so that a metal gate including a work function metal layer and a low resistivity material is formed, but it is not limited thereto. Moreover, the gate dielectric layer **220** may further include a buffer layer (not shown) located between the substrate **210** and a dielectric layer having a high dielectric constant. In other ways, the tri-gate MOSFET **200** may be a transistor having a polysilicon gate, or may be formed by applying a gate first process or etc.

The tri-gate MOSFET **200** in this embodiment includes the gate dielectric layer **220** having a “ Γ ” shaped cross-sectional profile, and a gate channel **C2** below therefore has a “ Γ ” shaped cross-sectional profile. In other words, the gate channel **C2** of the tri-gate MOSFET **200** has a gate channel composed of three surfaces corresponding to the “ Γ ” shape. Compared to the gate channel **C1** with only one surface (as shown in FIG. 1) of the planar transistor **100**, the tri-gate MOSFET **200** has the advantages of smaller volume and faster carrier mobility.

Furthermore, a fin-shaped structure may have different shapes. For example, the fin-shaped structure may be a fin-shaped structure **212** having vertical sidewalls, or a fin-shaped structure having taper sidewalls etc, and different processes may be needed to form fin-shaped structures having different shapes. The process for forming the fin-shaped structure **212** having vertical sidewalls and taper sidewalls are sequentially described in the following.

The method for forming the fin-shaped structure **212** having vertical sidewalls on the substrate **210** may include the following steps. FIGS. 3-4 schematically depict cross-sectional views of a method for forming a fin-shaped structure according to the second embodiment of the present invention.

As shown in FIG. 3, a bulk substrate **210'** is provided, and a hard mask layer **10** is formed thereon, wherein the hard mask layer **10** may include a pad oxide layer **12** and a nitride layer **14**. As shown in FIG. 4, the hard mask layer **10** is patterned to define the location for forming a fin-shaped structure in the bulk substrate **210'**. An etching process is performed to form a fin-shaped structure **212** in the bulk substrate **210'**. This means that the fabrication of forming the fin-shaped structure **212** on the substrate **210** is complete. In this embodiment, the hard mask layer **10** is removed in a later process after the fin-shaped structure **212** is formed, so that a tri-gate MOSFET can be formed in the following processes. There are three contact faces between the fin structure **212** and the following formed dielectric layer serving as a carrier channel of which width is wider than a channel width in conventional planar MOSFETs. When a driving voltage is applied, the tri-gate MOSFET produces an on-current twice higher than in conventional planar MOSFETs. In another embodiment, the hard mask layer **10** is reserved to form a fin field effect transistor (Fin FET), which is another kind of multi-gate MOSFET. Since the hard mask layer **10** is reserved

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in the fin field effect transistor, there are only two contact faces between the fin structure **212** and the following formed dielectric layer.

The present invention can also be applied to other semiconductor substrates. For example, a silicon-on-insulator substrate (not shown) is provided, and then a single crystalline silicon layer being a top part of the silicon-on-insulator substrate (not shown) is etched till an oxide layer being a middle part of the silicon-on-insulator substrate (not shown) is exposed, meaning that the fin-shaped structure formed on the silicon-on-insulator substrate (not shown) is finished.

In order to clarify the present invention, one single fin-shaped structure **212** is depicted in this embodiment, but the present invention can also be applied to a plurality of fin-shaped structures **212**.

According to the above, the fin-shaped structure **212** formed through aforesaid method has vertical sidewalls and the width of the fin-shaped structure **212** and the pitch between each of the fin-shaped structure **212** are hard to narrow due to the process limitations. One embodiment of the present invention for forming a fin-shaped structure having a taper profile is presented in the following, wherein the maximum width of the formed fin-shaped structure can approach 20 nanometers, and the pitch of each of the fin-shaped structures can approach 70 nanometers. Therefore, the devices formed by the fin-shaped structures of this embodiment can have better electrical performances and smaller sizes than in the previous embodiment.

FIGS. 5-10 schematically depict cross-sectional views of a method for forming a fin-shaped structure according to a third embodiment of the present invention. As shown in FIG. 5, a substrate **310** is provided, wherein the substrate **310** may be a semiconductor substrate such as a silicon substrate, a silicon containing substrate such as a silicon carbide substrate, a III-V group-on-silicon (such as GaN-on-silicon) substrate, a graphene-on-silicon substrate, a silicon-on-insulator (SOI) substrate or an epitaxial layer containing substrate such as a P-type substrate with a 2.5 μm P-type epitaxial layer. A pad layer **22** is formed on the substrate **310**, wherein the pad layer **22** may include an oxide layer, but it is not limited thereto. A sacrificial pattern material **24'** is formed to entirely cover the pad layer **22**. As shown in FIG. 6, the sacrificial pattern material **24'** is patterned to form a sacrificial pattern **24**. In this embodiment, the sacrificial pattern material **24'** is polysilicon, and the sacrificial pattern **24** is therefore a polysilicon gate, so that the forming method can be similar to the current process of a polysilicon gate, but it is not limited thereto.

As shown in FIGS. 7-8, a spacer **26** is formed on the pad layer **22** beside the sacrificial pattern **24**. More precisely, as shown in FIG. 7, a spacer material **26'** entirely covers the sacrificial pattern **24** and the pad layer **22**. Then, the spacer material **26'** is etched to form spacers **26** on the pad layer **22** beside the sacrificial pattern **24**. The spacer material **26'** may be silicon nitride, so the spacer **26** is therefore a nitride spacer, but it is not limited thereto.

It is emphasized that, the ratio of the height **h1** of the spacer **26** to the thickness **h2** of the pad layer **22** is larger than 5, so that a fin-shaped structure can be formed in the substrate **310** in later processes. In this embodiment, as the pad layer **22** is an oxide layer and the spacer **26** is a nitride spacer, the thickness of the pad layer **22** is preferred to be substantially 100~110 angstroms while the thickness of the spacer **26** is preferred to be substantially 800~900 angstroms, but it is not limited thereto. The relative height **h1** and thickness **h2** of the pad layer **22** and the spacer **26** and the materials of the pad layer **22** and the spacer **26** depend upon the height, the width and the pitch of the desired formed fin-shaped structures.

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As shown in FIG. 9, the sacrificial pattern 24 is removed, so that recesses R1 are formed on the pad layer 22 in the spacers 26. The method of removing the sacrificial pattern 24 may be an etching process P1, wherein the etching rate of the etching process P1 to the sacrificial pattern 24 is larger than to the spacers 26, so that the sacrificial pattern 24 can be removed while most of the spacers 26 is kept intact.

The layouts of the spacers 26 are transferred into the substrate 310, so that fin-shaped structures 312 are formed in the substrate 310 as shown in FIG. 10. In this embodiment, there are four fin-shaped structures 312; in another embodiment, the number of the fin-shaped structures 312 may be one or more than one. More precisely, the method of transferring the layout of the spacers 26 into the substrate 310 may be an etching process P2 using the spacers 26 as hard masks to etch the pad layer 22 and the substrate 310 downward, so that the fin-shaped structures 312 are formed. The etching process P2 may be a dry etching process, a wet etching process or the combination of both. In this embodiment, the etching process P2 is a fluoride-containing etching process, so that fluoride can accumulate on the sidewalls S1 and S2 of the fin-shaped structures 312 while etching, and the etching of the sidewalls S1 and S2 can therefore be restrained, thereby achieving fin-shaped structures 312 with oblique sidewalls; that is, the fin-shaped structures 312 have taper profiles. The materials of the sacrificial pattern 24, the pad layer 22, the spacer 26 and the substrate 310 and the etching processes P1 and P2 depend upon the sizes and the shapes etc. of the desired fin-shaped structures 312. Especially, the etching selectivities of the etching process P2 to the pad layer 22, the spacer 26 and the substrate 310 will dramatically affect the heights h3 and the shapes of the formed fin-shaped structures 312.

In this embodiment, the angles $\theta 1$ and $\theta 2$ between the sidewalls S1 and S2 of the fin-shaped structures 312 and the substrate 310 are less than 90 degree, so that the fin-shaped structures 312 have taper profiles. Preferably, the angles $\theta 1$ and $\theta 2$ between the sidewalls S1 and S2 of the fin-shaped structures 312 and the substrate 310 are of 70 degree, so that the fin-shaped structures 312 have taper profiles. Since the spacers 26 have a cambered surface S3, the angles $\theta 1$ and $\theta 2$ between the sidewalls S1 and S2 of the fin-shaped structures 312 and the substrate 310 can be different due to the boat-shaped profiles of the spacers 26, leading to different etching capabilities to the sidewalls S1 and S2 during the transfer of the layout of the spacers 26 into the substrate 310. Moreover, as the lengths l1 of the cambered surfaces S3 profiles of the spacers 26 are much shorter and the cross-sectional profiles of the spacers 26 are approximate rectangles, the angles $\theta 1$ and $\theta 2$ between the sidewalls S1 and S2 of the fin-shaped structures 312 and the substrate 310 are approximately the same. Therefore, the shapes of the fin-shaped structures 312 can be adjusted by adjusting the spacers 26.

It is emphasized that, the fin-shaped structures 312 in this embodiment can have shorter maximum width and shorter pitch Pt than the fin-shaped structures 212 in the second embodiment. The formed layout in this embodiment can therefore be refined, and the volume of the formed semiconductor component is reduced. More specifically, the maximum width w2 of the fin-shaped structures 312 in this embodiment (meaning the width of the bottoms of the fin-shaped structures 312) can approach the range of 5~20 nanometers. For example, the maximum width w2 of the fin-shaped structures 312 in this embodiment can be 10 nanometers. The pitch Pt between each of the fin-shaped structures 312 can approach 70 nanometers.

According to the above, the present invention provides a method for forming a fin-shaped structure, which transfers

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the layout of the spacer into the substrate to form at least a fin-shaped structure into the substrate, wherein the fin-shaped structure has a taper profile. More precisely, the method for forming a fin-shaped structure includes the following steps. A pad layer and a sacrificial pattern are sequentially formed on the pad layer. Spacers are formed on the pad layer beside the sacrificial pattern. The sacrificial pattern is removed. The layout of the spacers is transferred into the substrate, so that at least a fin-shaped structure having a taper profile is formed in the substrate. It is emphasized that, the ratio of the height of the spacer to the thickness of the pad layer is larger than 5, thereby forming the fin-shaped structure of the present invention. For instance, the maximum width of the fin-shaped structure can be comprised within 5~20 nanometers, such as 10 nanometers for example, and the pitch between each of the fin-shaped structures 312 can approach 70 nanometers.

Those skilled in the art will readily observe that numerous modifications and alterations of the device and method may be made while retaining the teachings of the invention. Accordingly, the above disclosure should be construed as limited only by the metes and bounds of the appended claims.

What is claimed is:

1. A method for forming a fin-shaped structure, comprising:

forming a pad layer on a substrate;

forming a sacrificial pattern on the pad layer;

forming a spacer on the pad layer beside the sacrificial pattern, wherein the ratio of the height of the spacer to the pad layer is larger than 5;

removing the sacrificial pattern completely; and

transferring the layout of the spacer into the substrate after the sacrificial pattern is completely removed, to form at least a fin-shaped structure having a taper profile in the substrate.

2. The method for forming a fin-shaped structure according to claim 1, wherein the pad layer comprises an oxide layer.

3. The method for forming a fin-shaped structure according to claim 1, wherein the step for forming the sacrificial pattern comprises:

entirely covering a sacrificial pattern material on the pad layer; and

patterning the sacrificial pattern material to form the sacrificial pattern.

4. The method for forming a fin-shaped structure according to claim 1, wherein the sacrificial pattern comprises a polysilicon gate.

5. The method for forming a fin-shaped structure according to claim 1, wherein the step for forming the spacer comprises: entirely covering a spacer material on the sacrificial pattern and the pad layer; and

etching the spacer material to form the spacer.

6. The method for forming a fin-shaped structure according to claim 1, wherein the pad layer comprises an oxide layer and the spacer comprises a nitride spacer.

7. The method for forming a fin-shaped structure according to claim 6, wherein the thickness of the pad layer is 100~110 angstroms and the thickness of the spacer is 800~900 angstroms.

8. The method for forming a fin-shaped structure according to claim 6, wherein removing the sacrificial pattern comprises performing an etching process, wherein the etching rate of the etching process to the sacrificial pattern is larger than to the spacer.

9. The method for forming a fin-shaped structure according to claim 1, wherein the method of transferring the layout of the spacer into the substrate comprises performing an etching process.

10. The method for forming a fin-shaped structure according to claim 9, wherein the etching process comprises a dry etching process, a wet etching process or the combination of both.

11. The method for forming a fin-shaped structure according to claim 9, wherein the etching process comprises a fluoride-containing etching process. 5

12. The method for forming a fin-shaped structure according to claim 1, wherein the angle between at least a sidewall of the fin-shaped structure and the substrate is less than 90 degree and thereby forming a fin-shaped structure having a taper profile. 10

13. The method for forming a fin-shaped structure according to claim 12, wherein the angle between at least a sidewall of the fin-shaped structure and the substrate is 70 degree thereby forming a fin-shaped structure having a taper profile. 15

14. The method for forming a fin-shaped structure according to claim 1, wherein the fin-shaped structure has two sidewalls, and the angles between the two sidewalls and the substrate are different. 20

15. The method for forming a fin-shaped structure according to claim 1, wherein the maximum width of the fin-shaped structure is comprised within a range of 5~20 nanometers.

16. The method for forming a fin-shaped structure according to claim 15, wherein the maximum width of the fin-shaped structure is 10 nanometers. 25

17. The method for forming a fin-shaped structure according to claim 1, wherein the pitch between each of the fin-shaped structures is 70 nanometers.

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